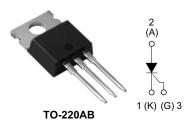


Vishay High Power Products

## Phase Control SCR, 10 A



| PRODUCT SUMMARY        |            |  |  |  |
|------------------------|------------|--|--|--|
| V <sub>T</sub> at 10 A | < 1.4 V    |  |  |  |
| I <sub>TSM</sub>       | 200 A      |  |  |  |
| $V_{RRM}$              | 800/1200 V |  |  |  |

### **DESCRIPTION/FEATURES**

The 16TTS.. High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS   |                     |                    |       |  |  |
|--|---------------------|--------------------|-------|--|--|
| APPLICATIONS   | SINGLE-PHASE BRIDGE | THREE-PHASE BRIDGE | UNITS |  |  |
| Capacitive input filter $T_A$ = 55 °C, $T_J$ = 125 °C, common heatsink of 1 °C/W | 13.5                | 17                 | А     |  |  |

| MAJOR RATINGS AND CHARACTERISTICS  |                              |             |       |  |  |
|------------------------------------|------------------------------|-------------|-------|--|--|
| PARAMETER                          | TEST CONDITIONS              | VALUES      | UNITS |  |  |
| I <sub>T(AV)</sub>                 | Sinusoidal waveform          | 10          | ٨     |  |  |
| I <sub>RMS</sub>                   |                              | 16          | Α     |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | Range (1)                    | 800/1200    | V     |  |  |
| I <sub>TSM</sub>                   |                              | 200         | A     |  |  |
| V <sub>T</sub>                     | 10 A, T <sub>J</sub> = 25 °C | 1.4         | V     |  |  |
| dV/dt                              |                              | 500         | V/µs  |  |  |
| dl/dt                              |                              | 150         | A/µs  |  |  |
| T <sub>J</sub>                     | Range                        | - 40 to 125 | °C    |  |  |

#### Note

<sup>(1)</sup> For higher voltage up to 1600 V contact factory

| VOLTAGE RATINGS   |      |      |    |  |  |  |
|---|------|------|----|--|--|--|
| PART NUMBER  V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V V DRM, MAXIMUM PEAK DIRECT VOLTAGE AT 12 |      |      |    |  |  |  |
| 16TTS08   | 800  | 800  | 10 |  |  |  |
| 16TTS12   | 1200 | 1200 | 10 |  |  |  |

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## 16TTS.. High Voltage Series

## Vishay High Power Products Phase Control SCR, 10 A



| ABSOLUTE MAXIMUM RATINGS                   |                    |   |                                      |  |      |                  |  |
|--|--------------------|---|--------------------------------------|--|------|------------------|--|
| PARAMETER                                  | SYMBOL             | TEGT COMPLETIONS  |                                      | VALUES                                 |      | UNITS            |  |
| PARAMETER                                  | STINIBUL           |   | TEST CONDITIONS                      |  | MAX. | UNITS            |  |
| Maximum average on-state current           | I <sub>T(AV)</sub> | T <sub>C</sub> = 98 °C, 1   | 80° conduction, half sine wave       | 10                                     |      |                  |  |
| Maximum RMS on-state current               | I <sub>RMS</sub>   |   |                                      | 1                                      | 6    | A                |  |
| Maximum peak, one-cycle,                   | 1                  | 10 ms sine p  | ulse, rated V <sub>RRM</sub> applied | 17                                     | 70   | A                |  |
| non-repetitive surge current               | I <sub>TSM</sub>   | 10 ms sine p  | ulse, no voltage reapplied           | 20                                     | 00   | 1                |  |
| Maximum 124 for fusing                     | l <sup>2</sup> t   | 10 ms sine p  | ulse, rated V <sub>RRM</sub> applied | 144                                    |      | A <sup>2</sup> s |  |
| Maximum I <sup>2</sup> t for fusing        | I-f                | 10 ms sine p  | ulse, no voltage reapplied           | no voltage reapplied 200               |      |                  |  |
| Maximum I <sup>2</sup> √t for fusing       | I <sup>2</sup> √t  | t = 0.1 to 10 r   | ns, no voltage reapplied             | 20                                     | 00   | A²√s             |  |
| Maximum on-state voltage drop              | $V_{TM}$           | 10 A, T <sub>J</sub> = 25 °C  |                                      | 1                                      | .4   | V                |  |
| On-state slope resistance                  | r <sub>t</sub>     | T 105 °C  |                                      | 24                                     | 1.0  | mΩ               |  |
| Threshold voltage                          | V <sub>T(TO)</sub> | T <sub>J</sub> = 125 °C   |                                      | 1                                      | .1   | V                |  |
| Maximum reverse and direct lockage current | 1 /1               | T <sub>J</sub> = 25 °C  | V Dated V A                          | 0                                      | .5   |                  |  |
| Maximum reverse and direct leakage current | $I_{RM}/I_{DM}$    | T <sub>J</sub> = 125 °C   | $V_R = Rated V_{RRM}/V_{DRM}$        | 1                                      | 0    |                  |  |
| Holding current                            | I <sub>H</sub>     | Anode supply = 6 V, resistive load, initial I <sub>T</sub> = 1 A 16TTS08, 16TTS12 |                                      | -                                      | 100  | mA               |  |
| Maximum latching current                   | ΙL                 | Anode supply = 6 V, resistive load  |                                      | Anode supply = 6 V, resistive load 200 |      | 00               |  |
| Maximum rate of rise of off-state voltage  | dV/dt              |   |                                      | 50                                     | 00   | V/µs             |  |
| Maximum rate of rise of turned-on current  | dl/dt              |   |                                      | 1                                      | 50   | A/μs             |  |

| TRIGGERING                                  |                   |   |        |       |  |
|---|-------------------|---|--------|-------|--|
| PARAMETER                                   | SYMBOL            | TEST CONDITIONS   | VALUES | UNITS |  |
| Maximum peak gate power                     | $P_{GM}$          |   | 8.0    | ۱۸/   |  |
| Maximum average gate power                  | $P_{G(AV)}$       |   | 2.0    | W     |  |
| Maximum peak positive gate current          | + I <sub>GM</sub> |   | 1.5    | Α     |  |
| Maximum peak negative gate voltage          | - V <sub>GM</sub> |   | 10     | V     |  |
|   | I <sub>GT</sub>   | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C        | 90     | mA    |  |
| Maximum required DC gate current to trigger |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C          | 60     |       |  |
|   |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C         | 35     |       |  |
|   |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C        | 3.0    |       |  |
| Maximum required DC gate voltage to trigger | $V_{\mathrm{GT}}$ | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C          | 2.0    | V     |  |
|   |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C         | 1.0    | V     |  |
| Maximum DC gate voltage not to trigger      | $V_{GD}$          | $T_J = 125 ^{\circ}\text{C},  V_{DRM} = \text{Rated value}$ 0.2 2.0 |        |       |  |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>   |   |        | mA    |  |

| SWITCHING                     |                 |                          |        |       |
|-------------------------------|-----------------|--------------------------|--------|-------|
| PARAMETER                     | SYMBOL          | TEST CONDITIONS          | VALUES | UNITS |
| Typical turn-on time          | t <sub>gt</sub> | T <sub>J</sub> = 25 °C   | 0.9    |       |
| Typical reverse recovery time | t <sub>rr</sub> | T <sub>.1</sub> = 125 °C | 4      | μs    |
| Typical turn-off time         | t <sub>q</sub>  | 1J = 125                 | 110    |       |

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## 16TTS.. High Voltage Series

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| THERMAL AND MECHANICAL SPECIFICATIONS           |         |                                   |                                      |             |            |
|---|---------|-----------------------------------|--------------------------------------|-------------|------------|
| PARAMETER                                       |         | SYMBOL                            | TEST CONDITIONS                      | VALUES      | UNITS      |
| Maximum junction and storage temperature range  |         | T <sub>J</sub> , T <sub>Stg</sub> |                                      | - 40 to 125 | °C         |
| Maximum thermal resistance, junction to case    |         | R <sub>thJC</sub>                 | DC operation                         | 1.3         |            |
| Maximum thermal resistance, junction to ambient |         | R <sub>thJA</sub>                 |                                      | 62          | °C/W       |
| Typical thermal resistance, case to heatsink    |         | R <sub>thCS</sub>                 | Mounting surface, smooth and greased | 0.5         |            |
| Approximate weight                              |         |                                   |                                      | 2           | g          |
|   |         |                                   |                                      | 0.07        | OZ.        |
| Mounting torque ———                             | minimum |                                   |                                      | 6 (5)       | kgf · cm   |
|   | maximum |                                   |                                      | 12 (10)     | (lbf ⋅ in) |
| Marking device                                  |         |                                   | Case style TO-220AB                  | 16T         | TS08       |
|   |         |                                   |                                      | 16T         | ΓS12       |

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## Vishay High Power Products Phase Control SCR, 10 A



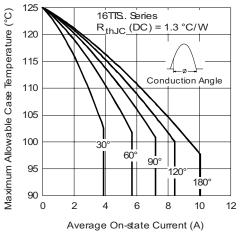


Fig. 1 - Current Rating Characteristics

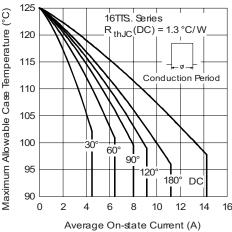


Fig. 2 - Current Rating Characteristics

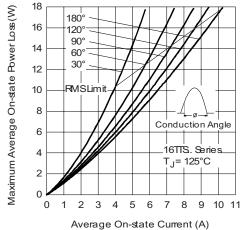


Fig. 3 - On-State Power Loss Characteristics

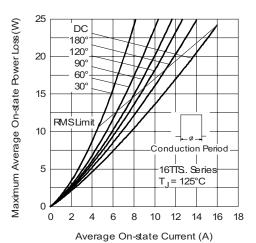


Fig. 4 - On-State Power Loss Characteristics

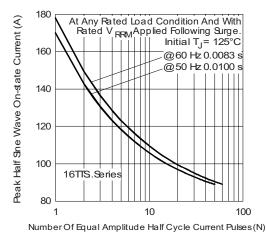


Fig. 5 - Maximum Non-Repetitive Surge Current

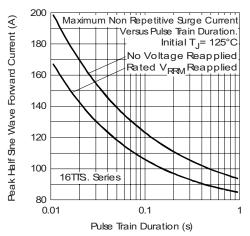


Fig. 6 - Maximum Non-Repetitive Surge Current



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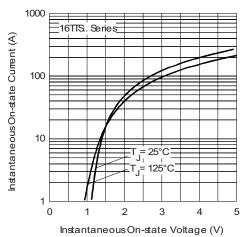


Fig. 7 - On-State Voltage Drop Characteristics

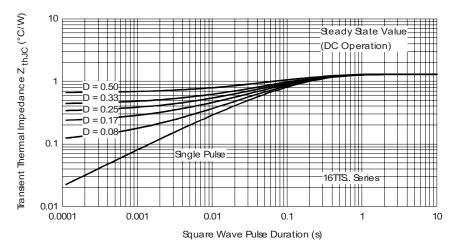


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

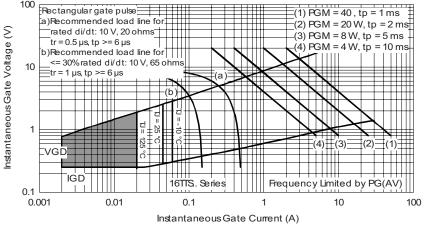


Fig. 9 - Gate Characteristics

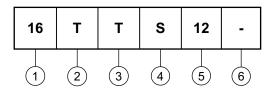
## 16TTS.. High Voltage Series

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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Current rating

2 - Circuit configuration:

T = Single thyristor

3 - Package:

T = TO-220AB

4 - Type of silicon:

S = Converter grade

5 - Voltage code x 100 = V<sub>RRM</sub>

08 = 800 V 12 = 1200 V

6 - • None = Standard production

• PbF = Lead (Pb)-free

Note: For higher voltage up to 1600 V contact factory

| LINKS TO RELATED DOCUMENTS                 |                                 |  |  |  |
|--|---------------------------------|--|--|--|
| Dimensions http://www.vishay.com/doc?95222 |                                 |  |  |  |
| Part marking information                   | http://www.vishay.com/doc?95225 |  |  |  |



Vishay

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Document Number: 91000 Revision: 18-Jul-08